

NTE5461 thru NTE5468 Silicon Controlled Rectifier (SCR) 10 Amp, TO220

Description:

The NTE5461 through NTE5468 series silicon controlled rectifiers are designed primarily for half—wave AC control applications such as motor controls, heating controls, and power supplies; or wherever half—wave silicon gate—controlled, solid—state devices are needed. These devices are supplied in a TO220 type package.

Features:

- Glass Passivated Junctions and Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation, and Durability
- Blocking Voltage to 800 Volts

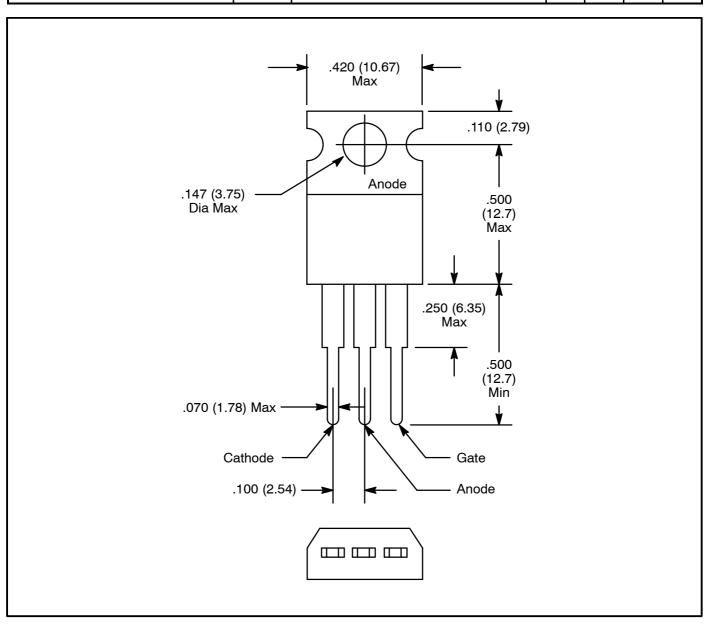
Absolute Maximum Ratings:

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Peak Repetitive Reverse Voltage; Peak Repetitive Off-State Voltage (Note 1), V _{RRM} , V _{DRM}
NTE5461
NTE5462
NTE5463
NTE5465
NTE5466
NTE5468
Non-Repetitive Peak Reverse Voltage; Non-Repetitive Off-State Voltage, V _{RSM} , V _{DSM}
NTE5461
NTE5462
NTE5463
NTE5465
NTE5466
NTE5468
RMS Forward Current (All Conducting Angles, T _C = +75°C), I _{T(RMS)}
Peak Forward Surge Current (1 Cycle, Sine Wave, 60Hz, T _C = +80°C), I _{TSM}
Circuit Fusing Considerations ($T_{.1} = -65^{\circ}$ to $+100^{\circ}$ C, $t = 1$ to 8.3ms), I^{2} t
Forward Peak gate Power ($t \le 10\mu s$), P_{GM}
Forward Average Gate Power, P _{G(AV)} 500mW
Operating Junction Temperature Range, T _J
Storage Temperature Range, T _{stg} 40° to +150°C
Thermal Resistance, Junction-to-Case, R _{thJC}

Note 1. V_{DRM} and V_{RRM} for all types can be applied on a continuous DC basis without incurring damage. Ratings apply for zero or negative gate voltage. Devices shall not have a positive bias applied to the gate concurrently with a negative potential on the anode.

Electrical Characteristics: $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit
Peak Forward or Reverse Blocking Current	I _{DRM} , I _{RRM}	Rated V _{DRM} or V _{RRM}	T _C = +25°C	_	_	10	μΑ
			T _C = +100°C	_	_	2	mA
Instantaneous On-State Voltage	V _T	I _{TM} = 30A _(Peak) , Pulse Width ≤ 1ms, Duty Cycle ≤ 2%		_	1.7	2.0	V
Gate Trigger Current (Continuous DC)	I _{GT}	$V_D = 12V$, $R_L = 30\Omega$		_	8	15	mA
Gate Trigger Voltage (Continuous DC)	V _{GT}	$V_D = 12V$, $R_L = 30\Omega$		_	0.9	1.5	V
Holding Current	lΗ	Gate Open, V _D = 12V, I _T = 150mA		_	10	20	mA
Gate Controlled Turn-On Time	t _{gt}	V_D = Rated V_{DRM} , I_{TM} = 2A, I_{GR} = 80mA		_	1.6	_	μs
Circuit Commutated Turn-Off Time	t _q	$V_D = V_{DRM}, \ I_{TM} = 2A, \ Pulse \ Width = 50\mu s, \ dv/dt = 200V/\mu s, \ di/dt = 10A/\mu s, \ T_C = +75^{\circ}C$		_	25	_	μs
Critical Rate-of-Rise of Off-State Voltage	dv/dt	V_D = Rated V_{DRM} , Exponential Rise, T_C = +100°C		_	100	_	V/μs



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